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(54) Title: METHOD OF REDUCING PATTERN COLLAPSE IN HIGH ASPECT RATIO NANOSTRUCTURES

(57) Abstract: A method is provided for treating the surface of high aspect ratio nanostructures to help protect the delicate nanostructures during some of the rigorous processing involved in fabrication of semiconductor devices. A wafer containing high aspect ratio nanostructures is treated to make the surfaces of the nanostructures more hydrophobic. The treatment may include the application of a primer that chemically alters the surfaces of the nanostructures preventing them from getting damaged during subsequent wet clean processes.. The wafer may then be further processed, for example a wet cleaning process followed by a drying process. The increased hydrophobicity of the nanostructures helps to reduce or prevent collapse of the nanostructures.

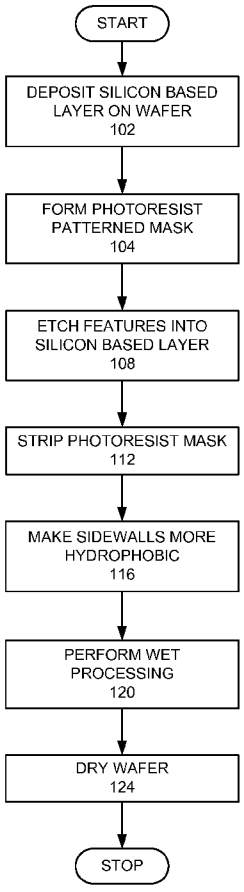


FIG. 1A

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